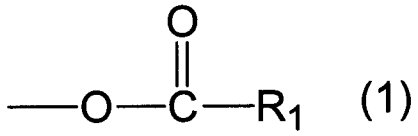
Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

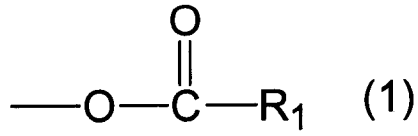
1. (Currently Amended) An underlayer coating forming composition comprising a dextrin ester compound ~~that~~ wherein at least 50% of hydroxy groups in the dextrin ~~is~~ are converted into ester groups of formula (1):



(1)

wherein R_1 is C_{1-10}alkyl group that may be substituted with hydroxy group, carboxyl group, cyano group, nitro group, C_{1-6}alkoxy group, fluorine atom, chlorine atom, bromine atom, iodine atom or C_{1-6}alkoxycarbonyl group, or a phenyl group, a naphthyl group or an anthryl group that may be substituted with C_{1-6}alkyl group, hydroxy group, carboxyl group, cyano group, nitro group, C_{1-6}alkoxy group, fluorine atom, chlorine atom, bromine atom, iodine atom or C_{1-6}alkoxycarbonyl group, a crosslinking compound, and an organic solvent.

2. (Currently Amended) An underlayer coating forming composition comprising a dextrin ester compound ~~that~~ wherein at least 50% of hydroxy groups in the dextrin is converted into ester groups of formula (1):



(1)

wherein R_1 is C_{1-10}alkyl group that may be substituted with hydroxy group, carboxyl group, cyano group, nitro group, C_{1-6}alkoxy group, fluorine atom, chlorine atom, bromine atom, iodine atom or C_{1-6}alkoxycarbonyl group, or a phenyl group, a naphthyl group or an anthryl group that may be substituted with C_{1-6}alkyl group, hydroxy group, carboxyl group, cyano group, nitro group, C_{1-6}alkoxy group, fluorine atom, chlorine atom, bromine atom, iodine

atom or C_{1-6}alkoxycarbonyl group~~has the same meaning as that defined in claim 1~~, ~~and that~~ wherein the dextrin ester compound has a weight average molecular weight of 4000 to 20000, and wherein the composition further comprises a crosslinking compound, and an organic solvent.

3. (Previously Presented) The underlayer coating forming composition according to claim 1, further comprising an acid compound or an acid generator.

4. (Currently Amended) A method for forming a photoresist pattern for use in manufacture of a semiconductor device, comprising ~~the steps of~~:

coating the underlayer coating forming composition according to claim 1 on a semiconductor substrate, and baking it to form an underlayer coating;

forming a photoresist layer on the underlayer coating;

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and

developing the photoresist layer after the exposure to light.

5. (Currently Amended) The underlayer coating forming composition according to claim 1, ~~in which~~wherein the composition is used for forming an underlayer coating by coating the composition on a semiconductor substrate having a hole with an aspect ratio shown in height/diameter of 1 or more, and baking it.

6. (Previously Presented) The underlayer coating forming composition according to claim 2, further comprising an acid compound or an acid generator.

7. (Currently Amended) A method for forming a photoresist pattern for use in manufacture of a semiconductor device, comprising ~~the steps of~~:

coating the underlayer coating forming composition according to claim 2 on a semiconductor substrate, and baking it to form an underlayer coating;

_____forming a photoresist layer on the underlayer coating;

_____exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and

_____developing the photoresist layer after the exposure to light.

8. (Currently Amended) A method for forming a photoresist pattern for use in manufacture of a semiconductor device, comprising ~~the steps of~~:

_____coating the underlayer coating forming composition according to claim 3 on a semiconductor substrate, and baking it to form an underlayer coating;

_____forming a photoresist layer on the underlayer coating;

_____exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and

_____developing the photoresist layer after the exposure to light.

9. (Currently Amended) The underlayer coating forming composition according to claim 2, ~~in which~~wherein the composition is used for forming an underlayer coating by coating the composition on a semiconductor substrate having a hole with an aspect ratio shown in height/diameter of 1 or more, and baking it.

10. (Currently Amended) A method for forming a photoresist pattern for use in manufacture of a semiconductor device, comprising ~~the steps of~~:

_____coating the underlayer coating forming composition according to claim 6 on a semiconductor substrate, and baking it to form an underlayer coating;

_____forming a photoresist layer on the underlayer coating;

_____exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and

_____developing the photoresist layer after the exposure to light.